ABSTRACT OF THE DISCLOSURE

PRODUCTION METHOD FOR A THIN FILM ON A SUPPORT AND STRUCTURE THUS OBTAINED

The present invention relates to a production method for a thin film on a support that includes an ionic implantation stage in order to demarcate the thin film in a substrate, the aim of the ionic implantation being to create a layer of micro-cavities in the substrate, a stage to bond the substrate to a support element using close contact and a heat treatment stage intended to bring the layer of micro-cavities to a temperature that is high enough to cause a split along said layer. At least one of said elements, substrate or support, is thinned before the heat treatment stage in order to maintain the close contact between the substrate and the support despite the stresses caused in the elements and resulting from the difference in their thermal dilation coefficients.

No Figures